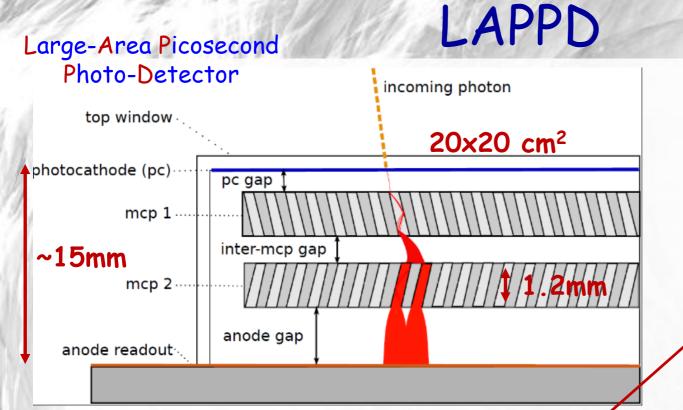
Development of the Large-Area Picosecond Photo-Detectors

Andrey Elagin
University of Chicago

Outline

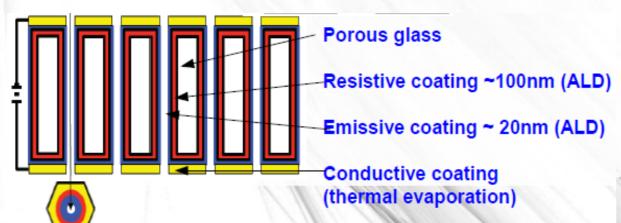
- · LAPPD Overview
- Commercialization status at Incom Inc.
- R&D Towards Volume Production
 - development of in-situ assembly process at UChicago
 - Gen-II LAPPD

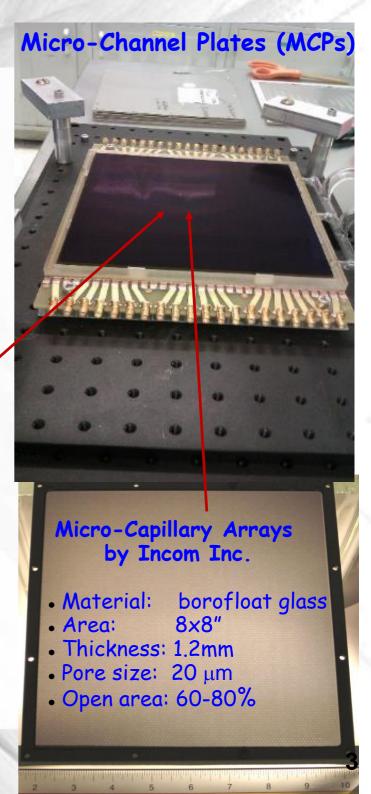


Atomic Layer Deposition (ALD)

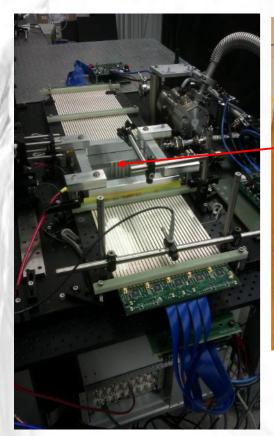
- J. Elam and A. Mane at Argonne (process is now licensed to Incom Inc.)

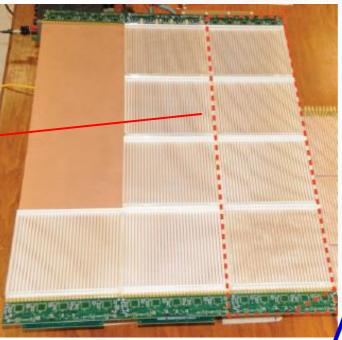
- Arradiance Inc. (independent process)

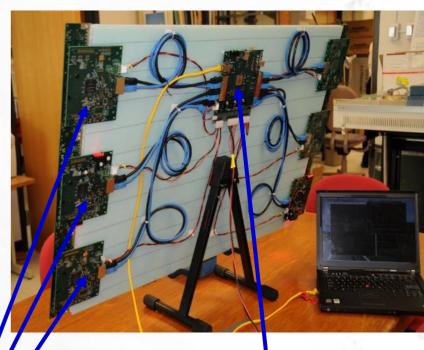




LAPPD Electronics







Delay-line anode NIM 711 (2013) 124

- 1.6 GHz bandwidth
- number of channels scales linearly with area

NIM 735 (2014) 452

PSEC-4 ASIC chip

- 6-channel, 1.5 GHz, 10-15 GS/s



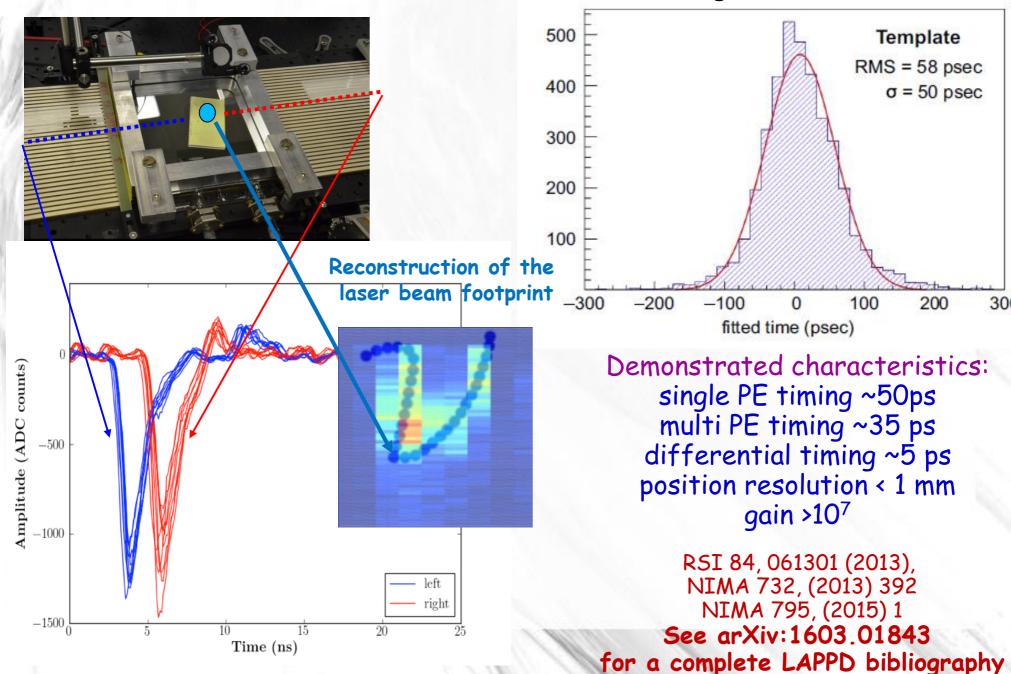
30-Channel ACDC Card (5 PSEC-4)



Central Card (4-ACDC;120ch)

LAPPD Prototype Testing Results

Single PE resolution



200

300

LAPPD Sealing Attempt @ SSL Berkeley

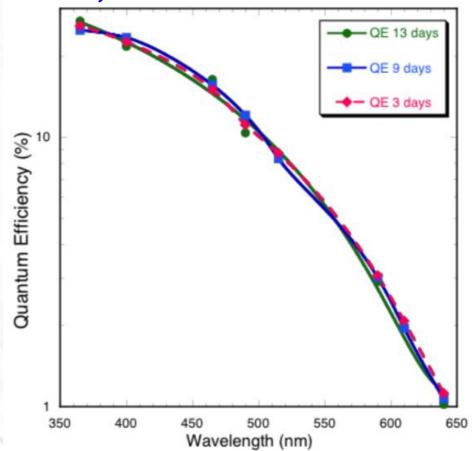


QE uniformity map

| 0.82 | | 0.99 | | 1.09 | |
|------|------|------|------|------|------|
| 0.83 | | 1.15 | | | 1.06 |
| | | 1.11 | | | |
| 0.89 | 0.95 | | 1.08 | | 1.11 |
| 0.84 | 0.85 | | 1.00 | | 0.99 |
| | | 0.92 | | | |
| 0.89 | | 1.07 | | | 0.94 |
| 0.95 | | 0.98 | | 0.89 | |

A fully processed ceramic LAPPD tile was tested while still in the vacuum chamber

- Peak QE ~25%
- QE non-uniformity +/-15% over 20x20 cm² area
- No change in QE after 2 weeks
- TTS ~ 200 ps (FWHM, using 80ps laser and ad-hoc connectors to get signal out of the vacuum chamber)



Commercialization Status

- April 2014 DOE funding to create infrastructure and demonstrate a pathway towards pilot production
- November 2015 Facility operational
- December 2015 Commissioning trial initiated
- · October 2016 First Sealed Tile with Bialkali Photocathode
- · Now transitioning from "commissioning" to "exploitation" stage



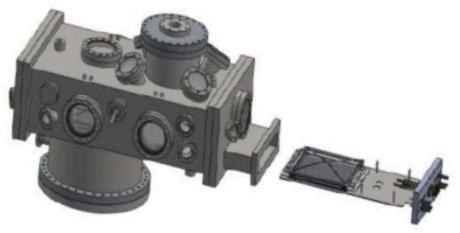
LAPPDTM @ Incom Inc.

Incom V2.0 LAPPD Integration & Sealing

Process & Hardware

Process:

- UHV with Conflat seals, scroll, turbo and ion pump.
- Tile kit components pre-assembled & locked in place.
- Baked to low 10⁻¹⁰ torr range
- In-tank operation of tile / scrubbing
- Window Transfer Process
- Multi-alkali Photocathode deposited on underside of window.
- Hot Indium Seal with grooved sidewalls

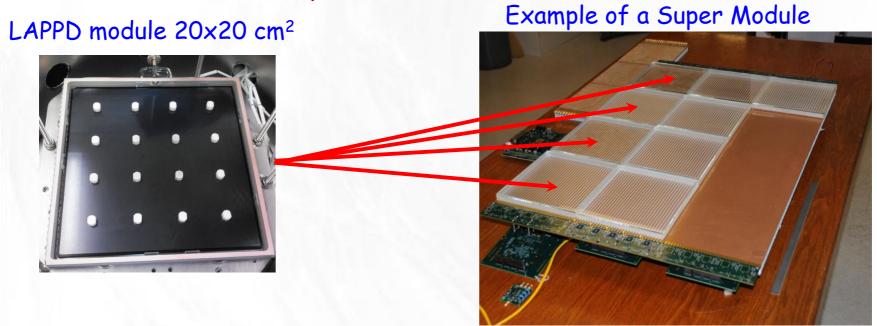


<u>Hardware:</u>

- Single "Fully Bakeable" Chamber: 30"L X 16"W X 8"H
- Simple window transfer between photocathode deposition & sealing.
- Electrical interconnects for inprocess monitoring
- Readily expandable for volume production

Goal of the R&D Effort at UChicago

Affordable large-area many-pixel photo-detector systems with picosecond time resolution



A production rate of 50 LAPPDs/week would cover 100m² in one year

- High volume production can be challenging
- We are exploring if a non-vacuum transfer process can be inexpensive and easier for a very high volume production

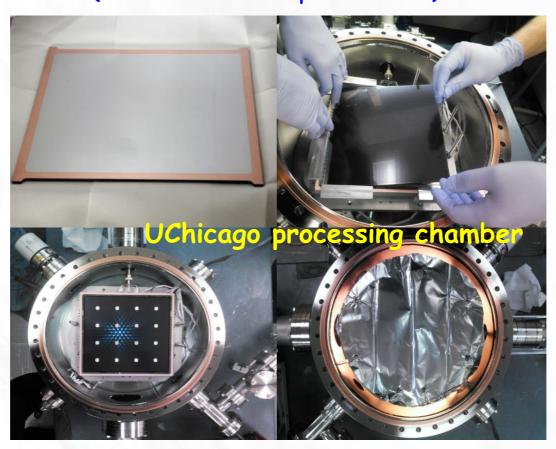
UChicago goal is to enable high volume production at Incom so we can do physics using LAPPD TM

In-Situ Assembly Strategy

Simplify the assembly process by avoiding vacuum transfer:

make photo-cathode after the top seal

(PMT-like batch production)



Step 1: pre-deposit Sb on the top window prior to assembly

Step 2: pre-assemble MCP stack in the tile-base

Step 3: do top seal and bake in the same heat cycle using dual vacuum system

Step 4: bring alkali vapors inside the tile to make photo-cathode

Step 5: flame seal the glass tube or crimp the copper tube

In-Situ Assembly Facility UChicago

The idea is to achieve volume production by operating many small-size vacuum processing chambers at the same time

Heat only the tile not the vacuum vessel

Intended for parallelization



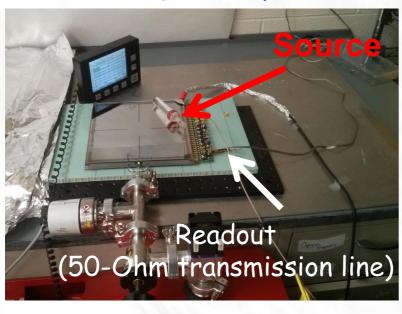
Looking forward towards transferring the in-situ process to industry

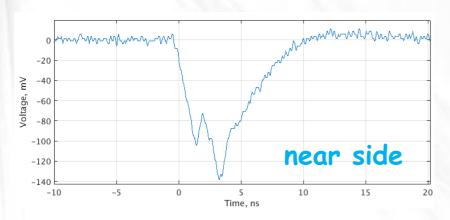
First Signals from an In-Situ LAPPD

April, 2016

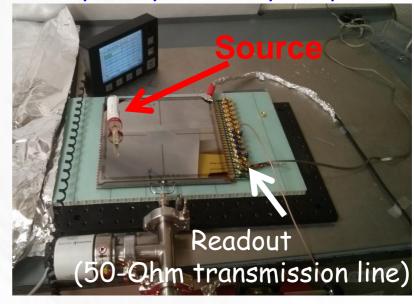
(Sb cathode)

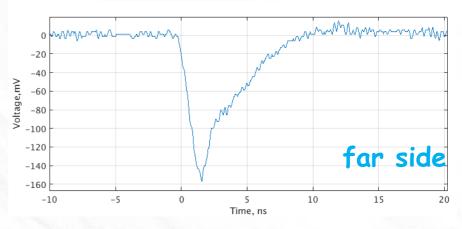
Near side: reflection from unterminated far end





Far side: reflection is superimposed on prompt





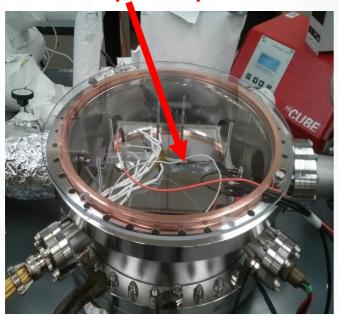
The tile is accessible for QC before photo-cathode shot Could help the production yield

July, 2016

1st In-Situ Photo-Cathode

Sb layer only

Cs-Sb photo-cathode



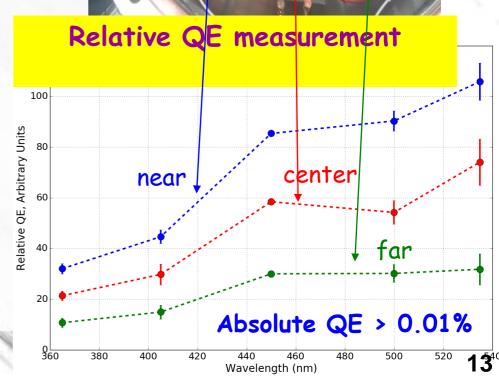
Cs

First in-situ commissioning run

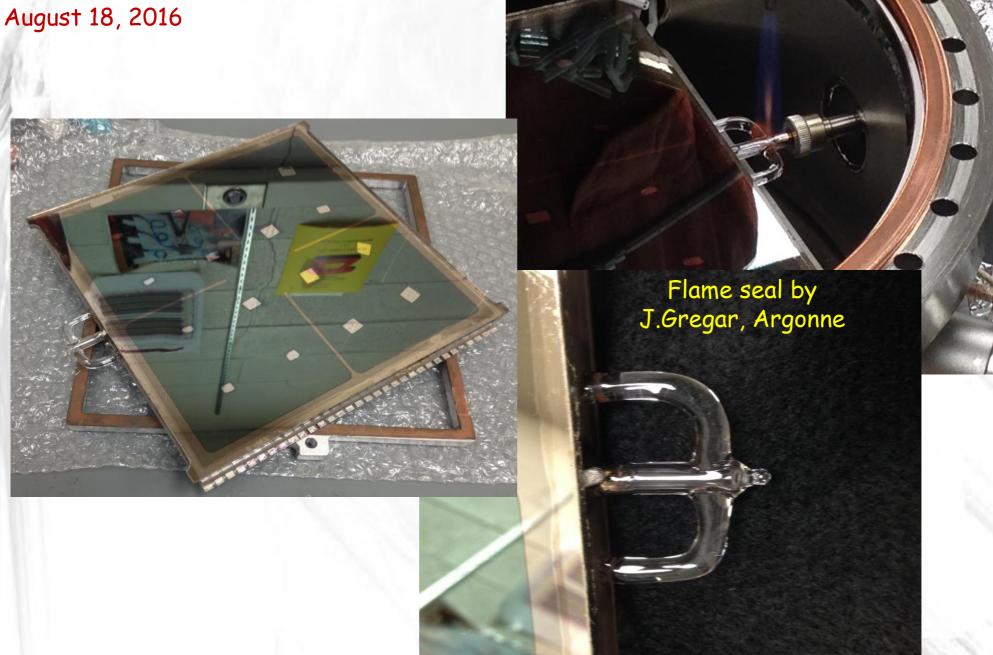
- saw first photo-current response from in-situ photo-cathode
- measured relative QE (absolute QE is tricky due to DC current through the whole stack)
- demonstrated a <u>sealed tile</u> configuration
 - no QE drop for 2 weeks after the valve to the pump was closed
 - no QE drop for 3 weeks after flame seal

Note on this commissioning run:

PC is very thick for transmission mode operation (initial 20nm of Sb translates into ~80nm of Cs-Sb)

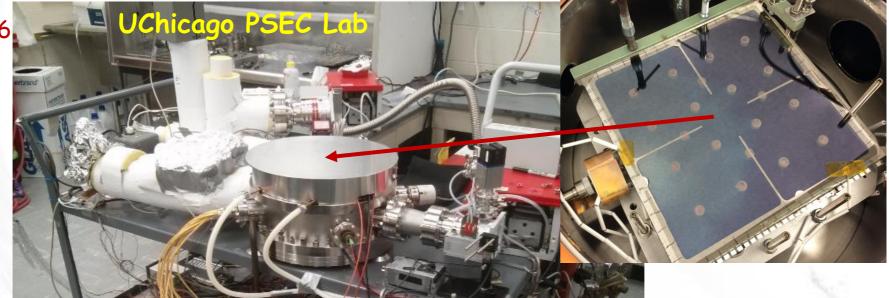


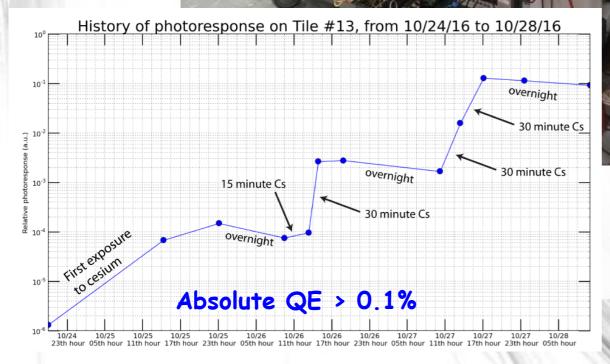
Flame Seal



2nd In-Situ Photo-Cathode

Oct - Nov, 2016

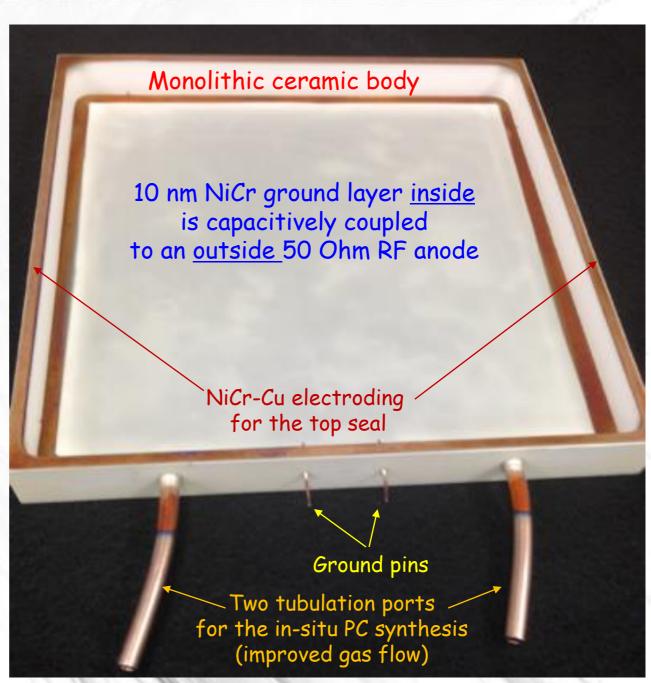




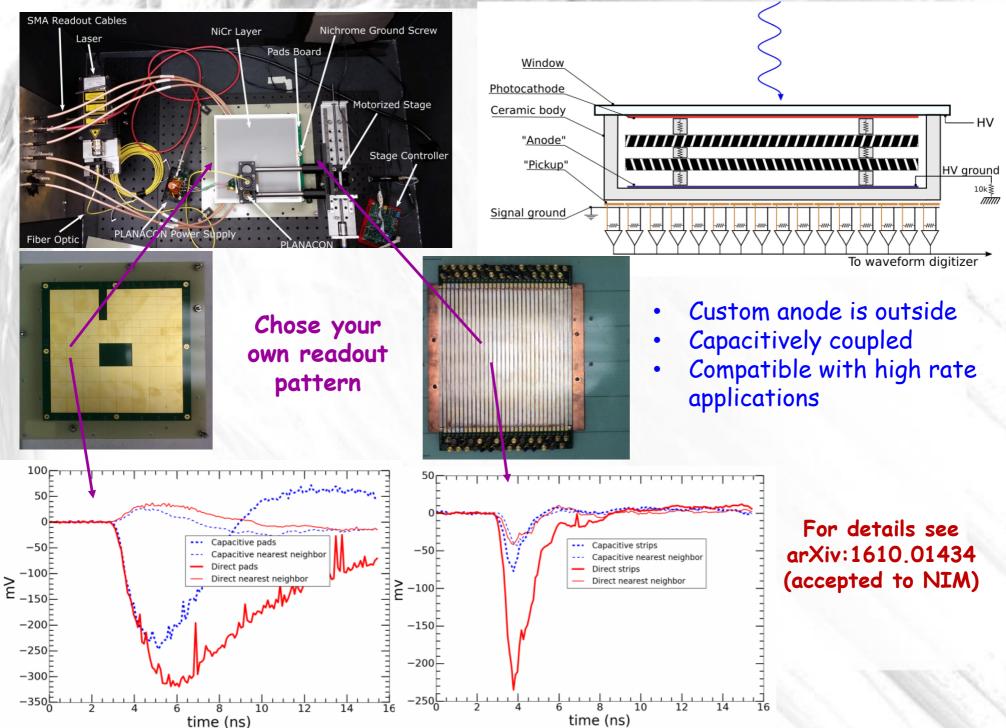
- Thinner Sb layer (~10nm)
- Improved instrumentation and process control
- A factor of 10 improvement in QE
- Currently doing life-time testing (flame sealed on Nov 16)

Gen-II LAPPD

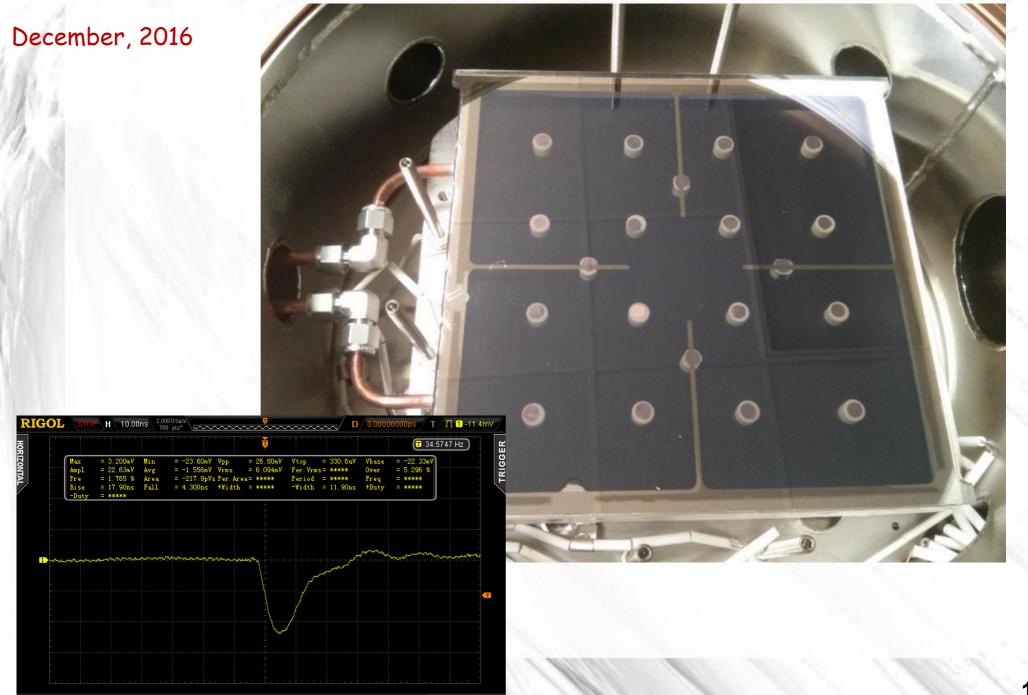
- Robust ceramic body
- Fused silica window
- Anode is not a part of the vacuum package
- Enables fabrication
 of a generic tile for
 different applications
- Compatible with in-situ and vacuum transfer assembly processes



Gen-II LAPPD: "inside-out" anode



Gen-II LAPPD: work in progress



Summary

- Commercialization at Incom Inc. goes well
 - recently demonstrated first sealed functional LAPPD with bi-alkali photo-cathode
 - transitioning from "commissioning" to "exploitation" stage
- With the goal to use LAPPDs in large experiments
 UChicago group is focused on R&D for high volume
 production process
- Making photo-cathode in-situ as a final step is very attractive
 - leak check before PC-synthesis
 - real-time tuning and optimization of PC is possible
- Right at the moment UC group is working on photo-cathode optimization and Gen-II LAPPD vacuum packaging
 - moving towards K2CsSb photo-cathode trials
 - building 2nd vacuum processing chamber -> parallelization



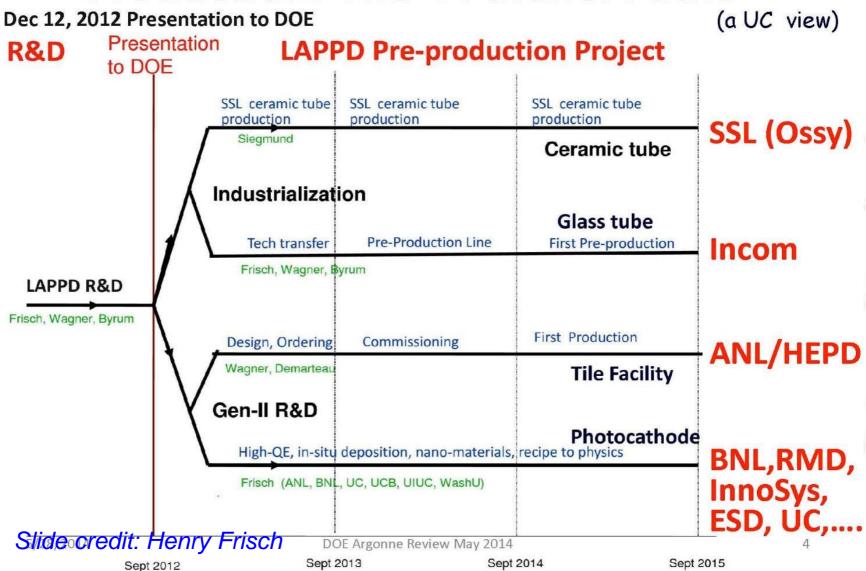
Early Adopters of LAPPD

Putting first LAPPD tiles into real experimental settings for testing is the highest priority

Some examples of early adopters:

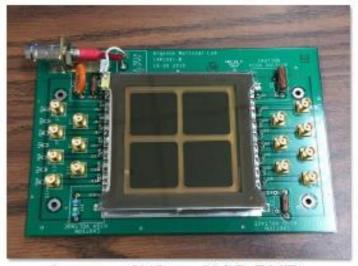
- ANNIE Accelerator Neutrino Neutron Interactions Experiment
- Cherenkov/Scintillation light separation for particle ID
- Optical Time Projection Chamber
- TOF measurements at Fermilab Test Beam
- There are many more (lots of interest shown at the "Early Adopters Meeting" hosted by Incom Inc. in 2013)

The 2013 Transition from LAPPD to Production: The 4 Parallel Paths

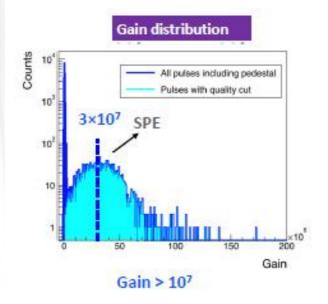


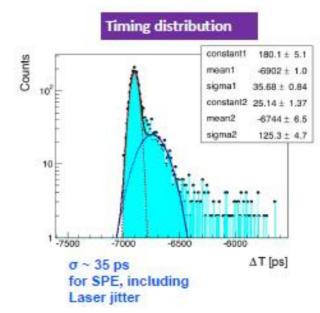
Argonne 6x6 cm² Photo-Detectors

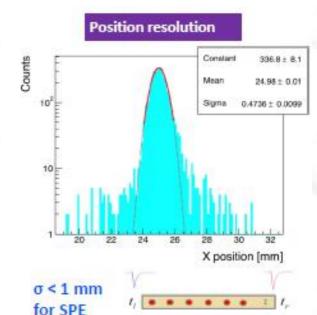
- Argonne routinely producing 6X6 cm² functional detectors with K₂CsSb photocathode
- New IBD-1 design allows HV optimization, as biasing individual components possible
- In addition to assembly of photo-detectors, laser testing facility available and photocathode research ongoing.
- Performance:
 - Gain > 10⁷
 - Quantum efficiency ~ 15%
 - Time resolution including the laser jitter: σ ~ 35 ps
 - Position resolution along anode strip: < 1 mm
 - Rate capability > 1 MHz/cm² for single photoelectrons



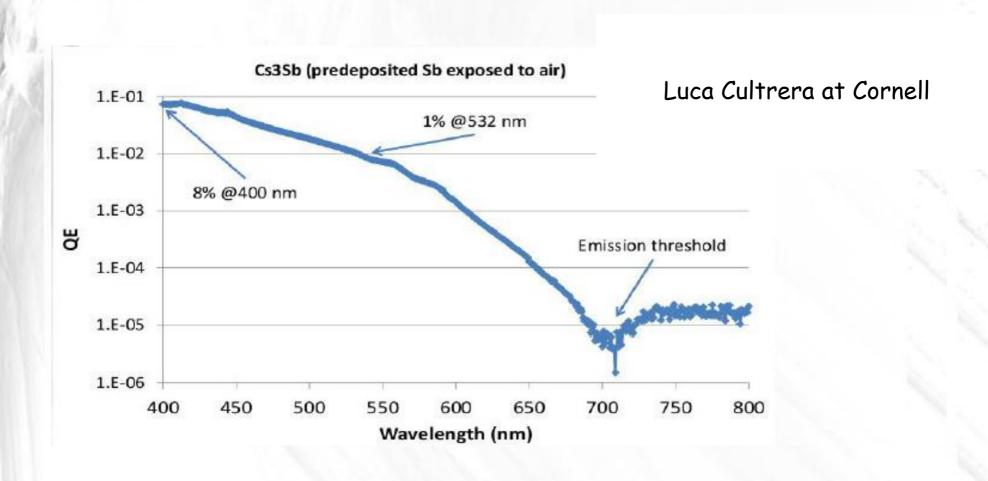
Argonne 6X6 cm MCP-PMT on custom readout board





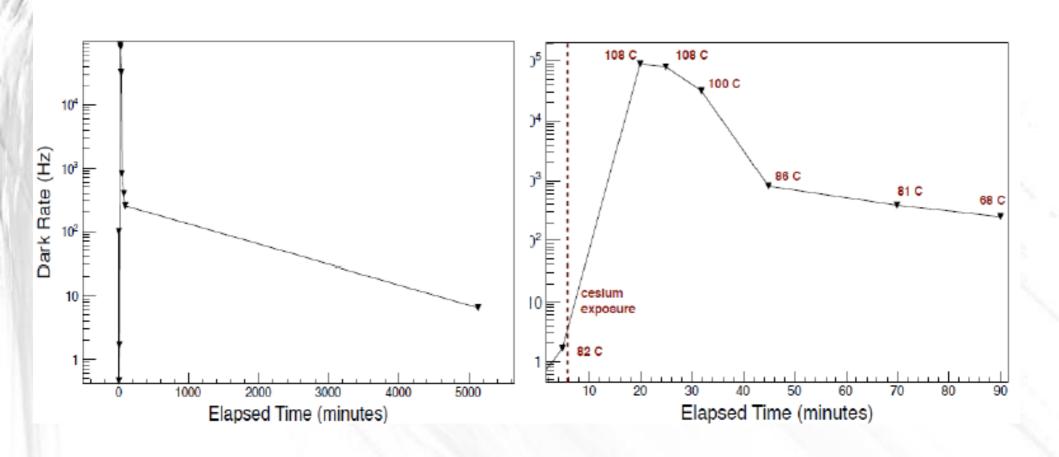


Can you make PC after Sb was exposed to air?



What about noise in the MCPs after Cs-ation?

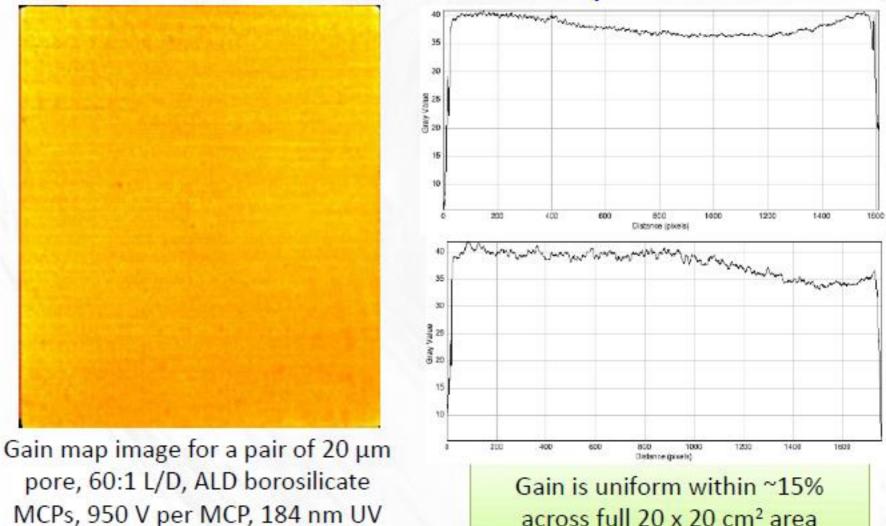
Matt Wetstein



SSL Ceramic LAPPD Tile Results

Measurements after full processing cycle inside the vacuum chamber QE 1.09 0.82 0.99 - QE 3 days 1.06 0.83 - Initial QE 1.15 Quantum Efficiency (%) 1.11 0.95 1.11 0.89 1.08 0.85 1.00 0.99 0.840.92 0.89 1.07 0.94 0.98 0.89 0.95 400 450 500 550 600 350 Wavelength (nm) Timing 85v Cap 145v Gap 230ps FWHM 212pg FWHM 257v Gap 400 800. High S/N Lase 64 pp FWHM FWHM (ps) 300 COUNTS 600 100 200 15 0 200 250 300 10.5 Time (ns) PC Gap Volts

Gain Uniformity



O.H.W. Siegmund, N. Richner, G. Gunjala, J.B. McPhate, A.S. Tremsin, H.J. Frisch, J. Elam, A. Mane, R. Wagner, C.A. Craven, M.J. Minot, "Performance Characteristics of Atomic Layer Functionalized Microchannel Plates" Proc. SPIE 8859-34, in press (2013).

In-Situ Process Pre-requisite

Reliable hermetic seal over a 90-cm long perimeter

Indium Solder Flat Seal Recipe

Two glass parts with flat contact surfaces

Process:

Input:

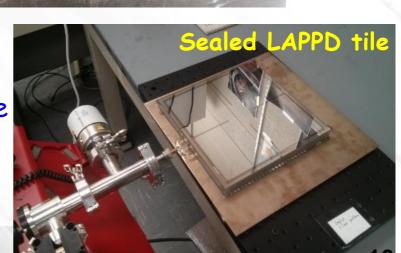
- Coat 200 nm of NiCr and 200 nm of Cu on each contact surface (adapted from seals by O.Siegmund at SSL UC Berkeley)
- Make a sandwich with indium wire
- Bake in vacuum at 250-300C for 24hrs

Key features:

- A good compression over the entire perimeter is needed to compensate for non-flatness and to ensure a good contact
- In good seals indium penetrates through entire NiCr layer (Cu always "dissolves")

This recipe is now understood

It works well over large perimeters



glass frame

(sidewall'

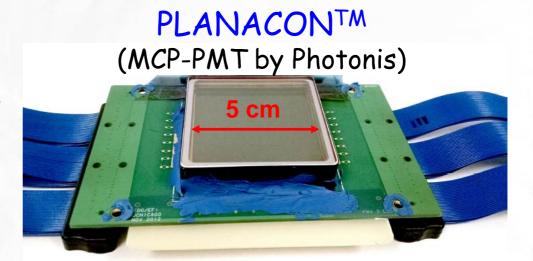
glass window

(8.66×8.66")

Metallization and compression are critical

Indium seal recipes exist for a long time

We adapted NiCr-Cu scheme from O.Siegmund at SSL UC Berkeley



Why do we need another indium seal recipe?

Make larger photo-detectors

Our recipe scales well to large perimeter

Simplify the assembly process

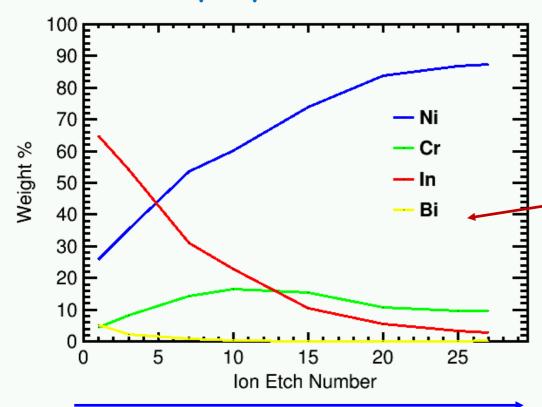
Our recipe is compatible with PMT-like batch production

Metallurgy of the Seal

Moderate temperatures and short exposure time:

- A thin layer of copper quickly dissolves in molten indium
 - Indium diffuses into the NiCr layer

Depth profile XPS



Layer depth (uncalibrated)

XPS access courtesy of J. Kurley and A. Filatov at UChicago

Low melting InBi alloy allows to explore temperatures below melting of pure In (157C)

Glass with NiCr-Cu metallization exposed to InBi at ~100C for <1hrs (it seals at these conditions)



InBi was scraped when still above melting (72C)

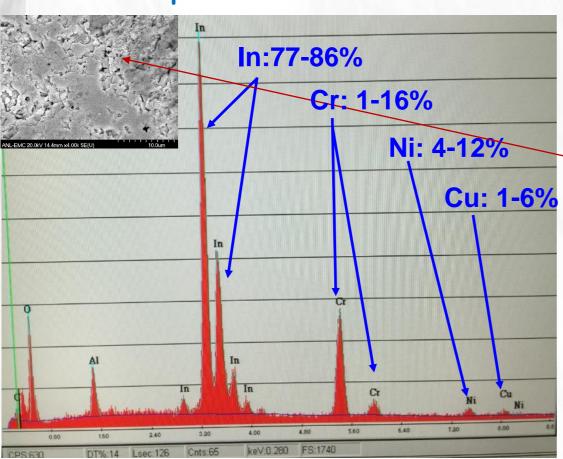
The ion etch number is a measure for the depth of each XPS run

Metallurgy of the Seal

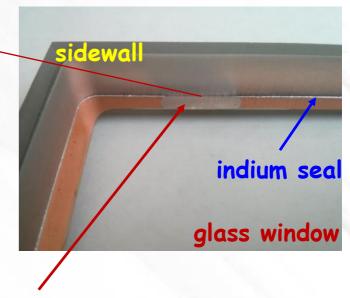
High temperatures and long exposure time

Indium penetrates through entire NiCr layer

SEM and EDAX of the metal surface scraped at the interface



Glass with NiCr-Cu metallization bonded by pure In at ~250C for 2hrs (it seals at these conditions)



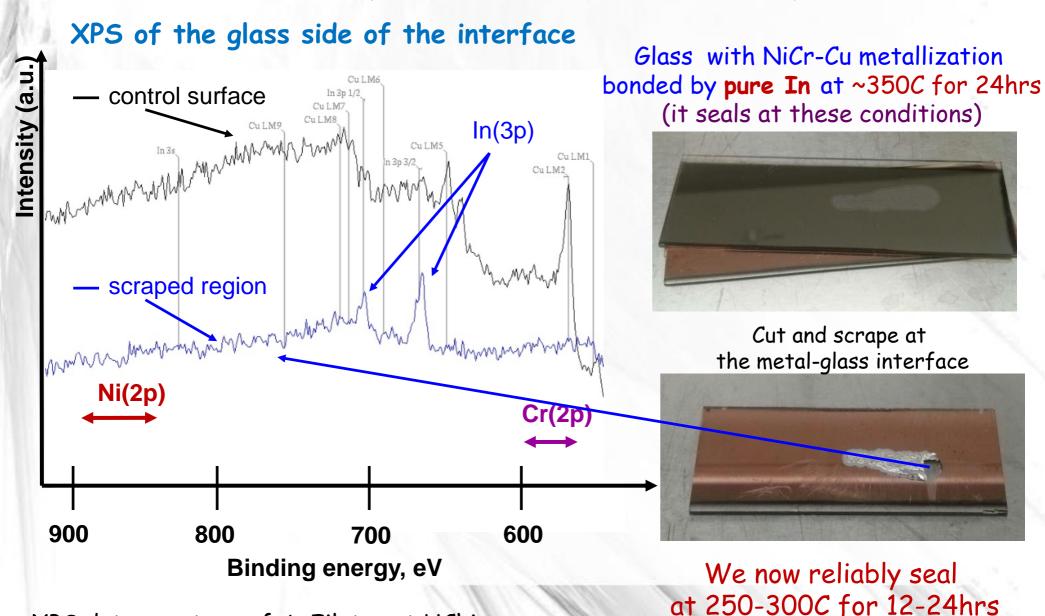
Cut and scrape at the metal-glass interface

SEM/EDAX data courtesy of J. Elam at Argonne

Metallurgy of a Good Seal

Higher temperatures and longer exposure time

Indium penetrates through entire NiCr layer



XPS data courtesy of A. Filatov at UChicago